

Digital Transistor	DTC(R1=R2 SERIES)CA
<p style="text-align: center;"><u>SOT-23</u></p>	<p>Features</p> <ul style="list-style-type: none"> Epitaxial planar die construction. Complementary PNP types available(DTA). Built-in biasing resistors,$R_1=R_2$. Also available in lead free version. <p>Application</p> <ul style="list-style-type: none"> The NPN style digital transistor.

ORDERING INFORMATION

Type No.	Marking	Package Code
DTC114ECA	24	SOT-23
DTC124ECA	25	SOT-23
DTC143ECA	23	SOT-23
DTC144ECA	26	SOT-23

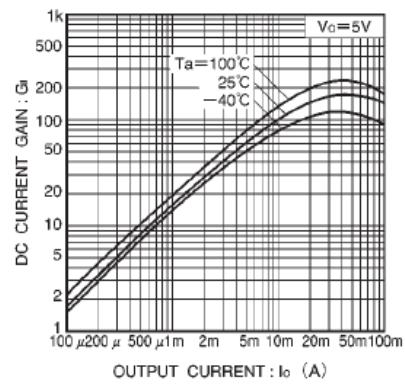
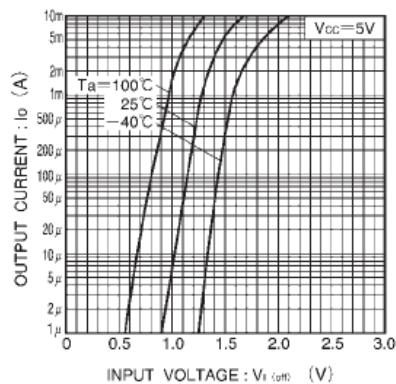
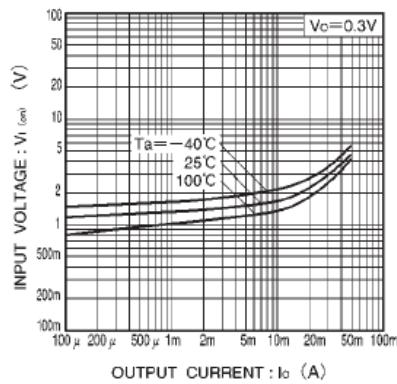
MAXIMUM RATING @ $T_a=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Value	Units
V_{CC}	Supply Voltage	50	V
V_{IN}	Input Voltage DTC114ECA	-10 to +40	V
	DTC124ECA	-10 to +40	
	DTC143ECA	-10 to +30	
	DTC144ECA	-10 to +40	
I_O	Output Current DTC114ECA	50	mA
	DTC124ECA	30	
	DTC143ECA	100	
	DTC144ECA	100	
$I_C(\text{Max.})$	Output current ALL	100	mA
P_D	Power Dissipation	200	mW
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient Air	625	°C/W
T_j, T_{stg}	Operating and Storage and Temperature Range	-55 to +150	°C

ELECTRICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Input Voltage	$V_{I(\text{off})}$	$V_{CC}=5\text{V}, I_O=100\mu\text{A}$	0.5	1.1	-	
Input Voltage	$V_{I(\text{on})}$	$V_O=0.3\text{V}, I_O=10\text{mA}$	-	1.9	3	V
		$V_O=0.2\text{V}, I_O=5\text{mA}$				
		$V_O=0.3\text{V}, I_O=20\text{mA}$				
		$V_O=0.3\text{V}, I_O=2\text{mA}$				
Output Voltage	$V_{O(\text{on})}$	$I_O/I_I=10\text{mA}/0.5\text{mA}$,	-	0.1	0.3	V
Input Current	I_I	$V_I=5\text{V}$	-	-	0.88 0.36 1.8 0.18	mA
Output Current	$I_O(\text{off})$	$V_{CC}=50\text{V}, V_I=0\text{V}$	-	-	0.5	μA
DC Current Gain	G_I	$V_O=5\text{V}, I_O=5\text{mA}$	30			
		$V_O=5\text{V}, I_O=5\text{mA}$	56			
		$V_O=5\text{V}, I_O=10\text{mA}$	20			
		$V_O=5\text{V}, I_O=5\text{mA}$	68			
Input Resistor	$R_1(R_2)$		7	10	13	
			15.4	22	28.6	
			3.29	4.7	6.11	
			32.9	47	61.1	$\text{k}\Omega$
Resistance Ratio	R_2/R_1	-	0.8	1	1.2	
Gain-Bandwidth Product	f_T	$V_{CE}=10\text{V}, I_E=-5\text{mA}$, $f=100\text{MHz}$	-	250	-	MHz

TYPICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified



单击下面可查看定价，库存，交付和生命周期等信息

[>>DIOS\(迪恩思\)](#)